

30V N-Channel Power MOSFET

 $30V, 50A, 9m\Omega$

FEATURES

- Fast switching
- Halogen Free
- G-S ESD Protection Diode Embedded

KEY PERFORMANCE PARAMETERS				
PARAMETER		VALUE	UNIT	
$V_{ extsf{DS}}$		30	V	
R _{DS(on)} (max)	V _{GS} = 10V	9	0	
	$V_{GS} = 4.5V$	14	mΩ	
Q_g		7.5	nC	

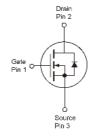
APPLICATION

- MB / VGA / Vcore
- POL Applications
- SMPS 2nd SR









Notes: Moisture sensitivity level: level 3. Per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T _C = 25°C unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	30	V	
Gate-Source Voltage		V_{GS}	±20	V	
Ossilia sa a Busia Ossal	$T_C = 25^{\circ}C$	I _D	50	А	
Continuous Drain Current	$T_C = 100$ °C		32		
Pulsed Drain Current (Note 1)		I _{DM}	200	Α	
Total Power Dissipation	T _C = 25°C		40	W	
	Derate above T _C = 25°C	P_{D}	0.32	W/°C	
Single Pulsed Avalanche Energy (Note 2)		E _{AS}	45	mJ	
Single Pulsed Avalanche Current (Note 2)		I _{AS}	30	Α	
Operating Junction Temperat	ure	T_J	150	°C	
Storage Temperature Range		T _{STG}	- 55 to +150	°C	



THERMAL PERFORMANCE				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction to Case Thermal Resistance	R _{eJC}	3.1	°C/W	
Junction to Ambient Thermal Resistance	R _{OJA}	62	°C/W	

Notes: $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. $R_{\Theta JA}$ is guaranteed by design while $R_{\Theta CA}$ is determined by the user's board design. $R_{\Theta JA}$ shown below for single device operation on FR-4 PCB in still air.

ELECTRICAL SPECIFICATIONS (T _J = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static (Note3)	<u>, </u>					
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV _{DSS}	30			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, \ I_D = 250 \mu A$	$V_{GS(TH)}$	1.2	1.6	2.5	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±10	μΑ
· · · - · · -	$V_{DS} = 30V$, $V_{GS} = 0V$	1			1	
Zero Gate Voltage Drain Current	$V_{DS} = 24V, T_J = 125^{\circ}C$	I _{DSS}			10	μΑ
Forward Transconductance	$V_{DS} = 10V, I_{D} = 8A$	g _{fs}		9.5		S
Davis Os and Os Olate Basista	$V_{GS} = 10V, I_D = 16A$	R _{DS(ON)}		7.5	9	mΩ
Drain-Source On-State Resistance	$V_{GS} = 4.5V, I_D = 8A$			9.6	14	
Dynamic (Note4)						
Total Gate Charge		Q_g		7.7		
Gate-Source Charge	$V_{DS} = 15V, I_{D} = 20A,$	Q_gs		1.9		nC
Gate-Drain Charge	$V_{GS} = 4.5V$	Q_{gd}		2.8		1
Input Capacitance		C _{iss}		680		
Output Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$	C _{oss}		150		pF
Reverse Transfer Capacitance	f = 1MHz	C_{rss}		70		
Gate Resistance	V_{GS} =0V, V_{DS} =0V, f=1MHz	R_g		2.7		Ω
Switching (Note5)						
Turn-On Delay Time		t _{d(on)}		4.8		
Turn-On Rise Time	$\begin{aligned} &V_{\text{DD}}\text{=}15\text{V} \text{ , } V_{\text{GS}}\text{=}10\text{V} \text{ ,} \\ &R_{\text{G}}\text{=}3.3\Omega \text{, } I_{\text{D}}\text{=}\text{-}15\text{A} \end{aligned}$	t _r		12.5		
Turn-Off Delay Time		t _{d(off)}		27.6		ns
Turn-Off Fall Time		t _f		8.2		
Source-Drain Diode (Note3)		•		•		•
Forward Voltage	$V_{GS} = 0V, I_{S} = 1A$	V _{SD}			1	V
Continuous Drain-Source Diode	$V_G=V_D=0V$	Is			50	Α
Pulse Drain-Source Diode	Force Current	I _{SM}			200	Α

Notes:

- 1. Repetitive Rating: Pulsed width limited by maximum junction temperature.
- 2. V_{DD} =25V, V_{GS} =10V, L=0.1mH, I_{AS} =30A, R_{G} =25 Ω , Starting T_{J} =25 $^{\circ}$ C.
- 3. Pulse test: PW ≤ 300µs, duty cycle ≤ 2%
- 4. For DESIGN AID ONLY, not subject to production testing.
- 5. Switching time is essentially independent of operating temperature

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ORDERING INFORMATION

PART NO.	PACKAGE	PACKING
TSM090N03ECP ROG	TO-252	2,500pcs / 13" Reel

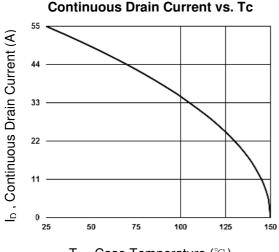
Note:

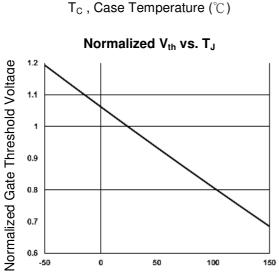
- 1. Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- 2. Halogen-free according to IEC 61249-2-21 definition



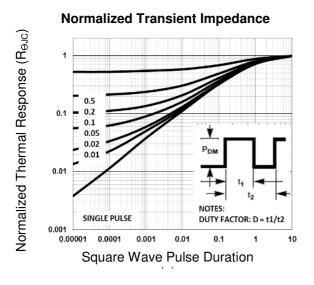
CHARACTERISTICS CURVES

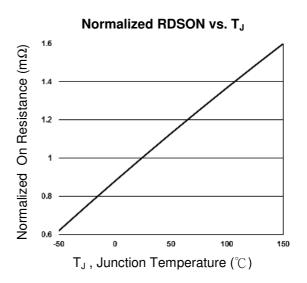
 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$

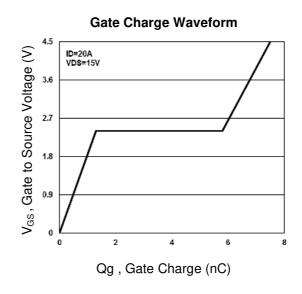


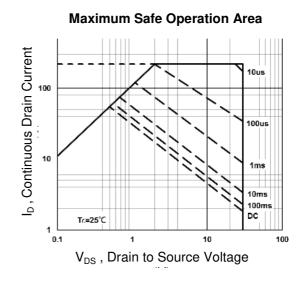


 T_J , Junction Temperature ($^{\circ}$ C)



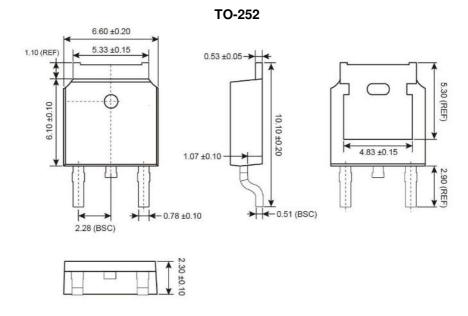




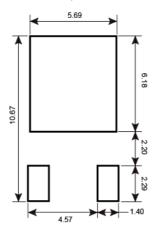




PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



SUGGESTED PAD LAYOUT (Unit: Millimeters)



MARKING DIAGRAM



Y = Year Code

M = Month Code for Halogen Free Product

O =Jan P =Feb Q =Mar R =Apr S =May T =Jun U =Jul V =Aug

W =Sep X =Oct Y =Nov Z =Dec

L = Lot Code



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